



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

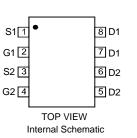
Features

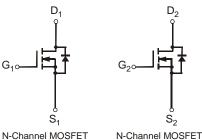
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)







Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 85°C	I _D	7.63 4.92	А
Pulsed Drain Current (Note 4)			IDM	30	A

SO-8

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	PD	1.16	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	$R_{ ext{ heta}JA}$	107.4	°C/W
Operating and Storage Temperature Range	$T_{J,} T_{STG}$	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on FR-4 PCB with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by function temperature.



Electrical Characteristics @T_A = 25°C unless otherwise specified

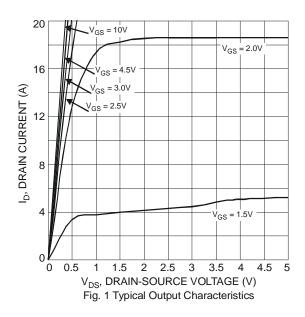
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)			-			
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T _J = 25°C	IDSS	-	-	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Р		19	28	mΩ	$V_{GS} = 4.5V, I_D = 6.0A$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	25	41		V _{GS} = 2.5V, I _D = 5.2A
Forward Transfer Admittance	Y _{fs}	-	6	-	S	$V_{DS} = 10V, I_D = 6A$
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 1.7A
DYNAMIC CHARACTERISTICS						*
Input Capacitance	Ciss	-	550	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Output Capacitance	C _{oss}	-	88	-		
Reverse Transfer Capacitance	Crss	-	81	-		
Gate Resistance	Rg	-	1.34	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (10V)	Qg	-	15.6	-	nC	$V_{GS} = 10V, V_{DS} = 10V,$ $I_D = 6.0A$
Total Gate Charge (4.5V)	Qg	-	7.2	-		
Gate-Source Charge	Q _{qs}	-	1.0	-	nC	$V_{GS} = 4.5 V, V_{DS} = 10V,$ $I_D = 6.0A$
Gate-Drain Charge	Q _{gd}	-	1.9	-		
Turn-On Delay Time	t _{D(on)}	-	4.69	-		$V_{DD} = 10V, V_{GEN} = 4.5V,$ $R_g = 1\Omega, I_D = 6.7A$
Turn-On Rise Time	tr	-	13.19	-		
Turn-Off Delay Time	t _{D(off)}	-	22.10	-	ns	
Turn-Off Fall Time	t _f	-	6.43	-		

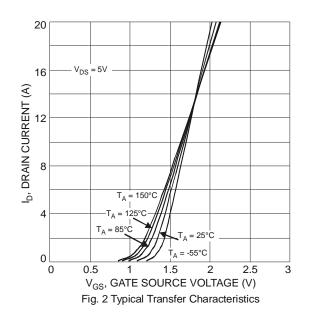
Notes:

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5. Short duration pulse test used to minimize self-heating effect.

6. Guaranteed by design. Not subject to production testing.

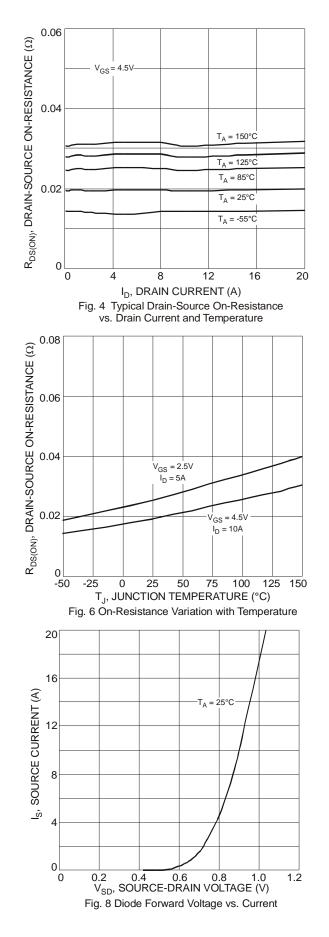






0.06 $R_{\text{DS}(\text{ON})},$ DRAIN-SOURCE ON-RESISTANCE ($\Omega)$ 0.05 1.8 V_{GS} 0.04 0.03 = 2.5 V_{GS} 0.02 = 10V V_{GS} V_{GS} 4.5 0.01 0 4 8 12 16 I_D, DRAIN-SOURCE CURRENT (A) 0 20 Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage 1.6 ON-RESISTANCE (NORMALIZED) 1.4 R_{DS(ON)}, DRAIN-SOURCE 1.2 1.0 = 4.5V GS = 10A I_D 0.8 V_{GS} = 2.5V $I_D = 5A$ 0.6 -25 50 75 100 125 0 25 150 T_J, JUNCTION TEMPERATURE (°C) Fig. 5 On-Resistance Variation with Temperature 1.6 $I_D = 1mA$ = 250µA 0 125 150 -50 25 50 75 100 -25 0

 $\rm T_A,$ AMBIENT TEMPERATURE (°C) Fig. 7 Gate Threshold Variation vs. Ambient Temperature

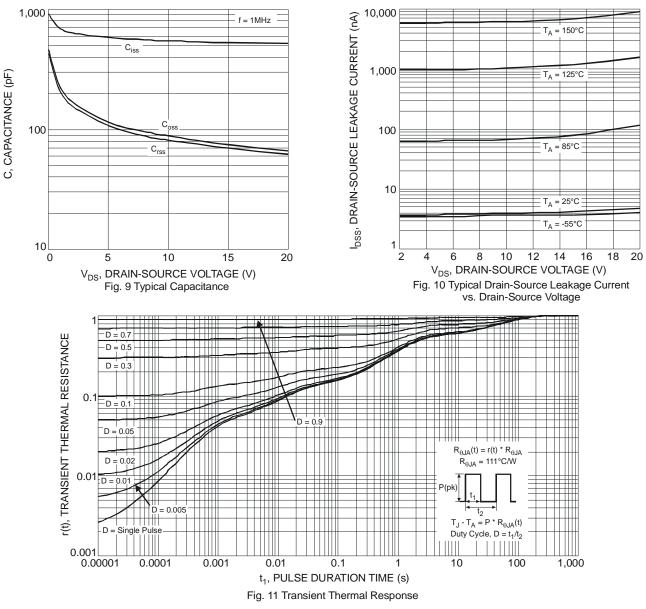


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DMN2041LSD Document number: DS31964 Rev. 2 - 2



DMN2041LSD

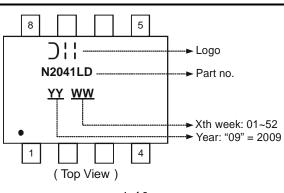


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN2041LSD-13	SO-8	2500/Tape & Reel

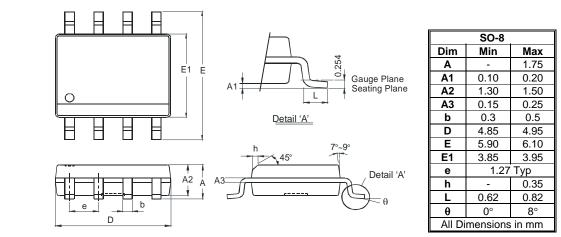
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

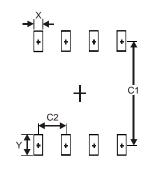




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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